VUTL010R11ANA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
100V	105mΩ@10V	15A

Symbol

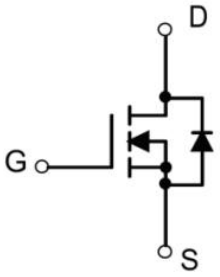


Figure 1 Symbol of VUTL010R11ANA

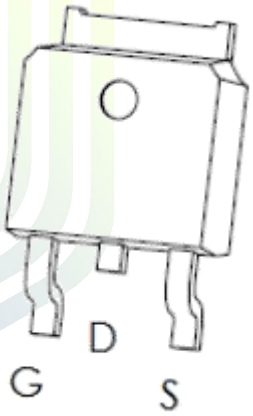
Features

- Excellent package for good heat dissipation
- Low reverse transfer capacitance
- Fast switching capability

Application

- Power switching application

Package Type



TO-252

Figure 2 Package Type of VUTL010R11ANA

Ordering Information

Product Name	Package
VUTL010R11ANA	TO-252

Absolute Maximum Ratings (T_C= 25 ºC, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current[Note1]	I_D	15	A
Pulsed Drain Current [Note2]	I_{DM}	45	
Single Pulsed Avalanche Energy[Note5]	E_{AS}	12	mJ
Total Power Dissipation[Note4]	P_D	1.25	W
Junction Temperature	T_J	150	ºC
Storage Temperature	T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient[Note6]	$R_{\theta JA}$		100		ºC/W

Electrical Characteristics (T_C= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 80V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note3]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	2.0	3.0	V
Static Drain-Source On-Resistance[Note3]	$R_{DS(ON)}$	V_{GS}=10V, I_D= 8A		76	105	mΩ
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=30V		580		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		50		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		40		pF
Total Gate Charge	Q_g	V_{DS}=30V		17		nC
Gate-Source Charge	Q_{gs}	V_{GS}=10V		4		
Gate-Drain Charge	Q_{gd}	I_D= 3A		5		
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 30V		13		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		8		
Turn-off Delay Time	$t_{d(off)}$	I_D= 2A		25		
Turn-off Fall Time	t_f	R_G=2.5Ω, R_L=15Ω		11		
Diode Characteristics						
Diode Forward Voltage [Note3]	V_{SD}	V_{GS}=0V, I_S= 8A		0.85	1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink.

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

4.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

5.V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=7A,Starting T_J=25°C

6. Device mounted on 1in2 FR-4 board with 1oz. Copper, in a still air environment with T_A =25°C.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

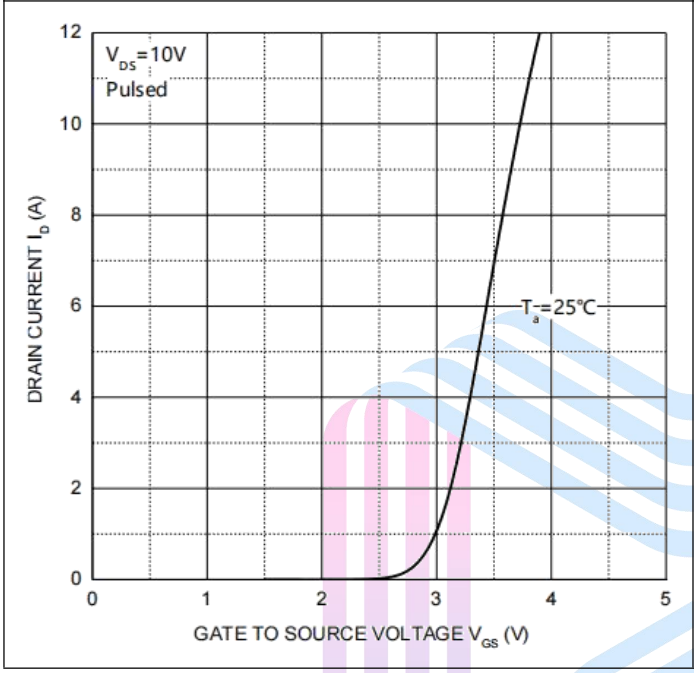


Figure 4: Output Characteristics

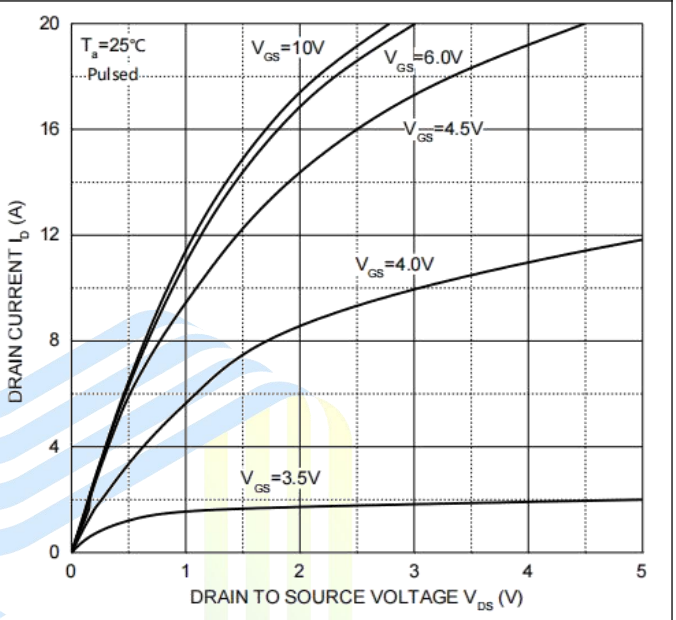


Figure 5: On-Resistance vs. Drain Current

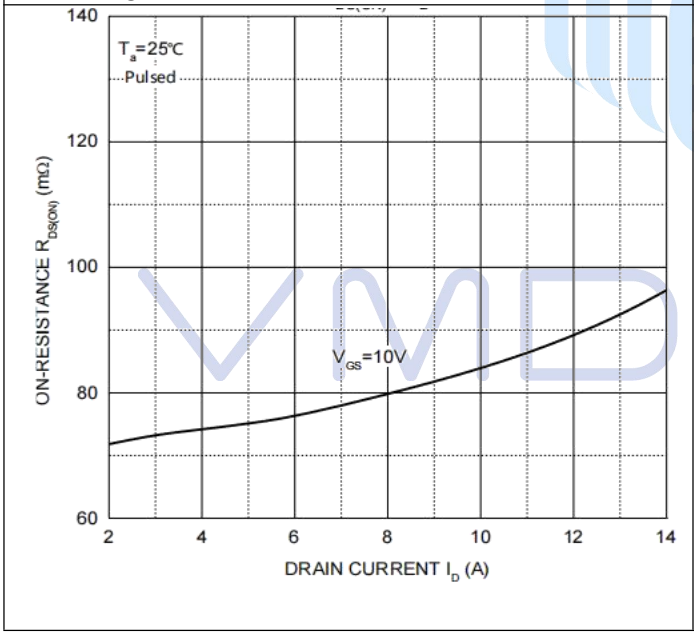


Figure 6: On-Resistance vs. Gate Voltage

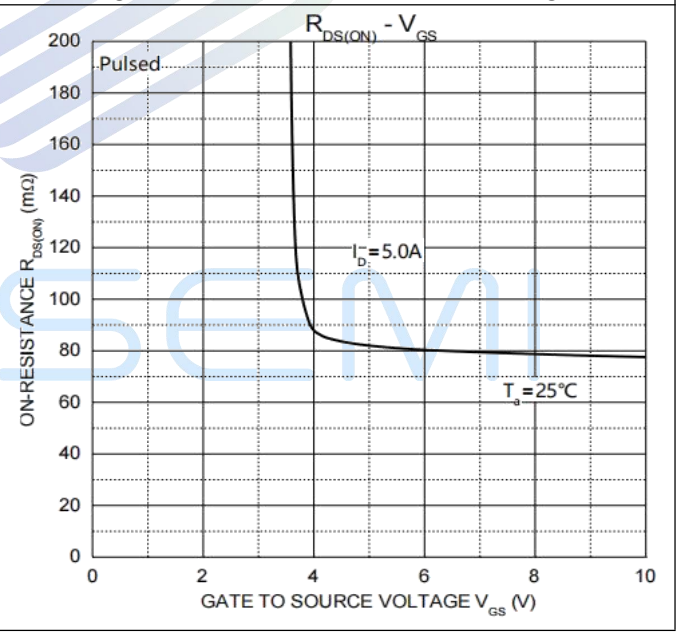


Figure 7: Body Diode Characteristics

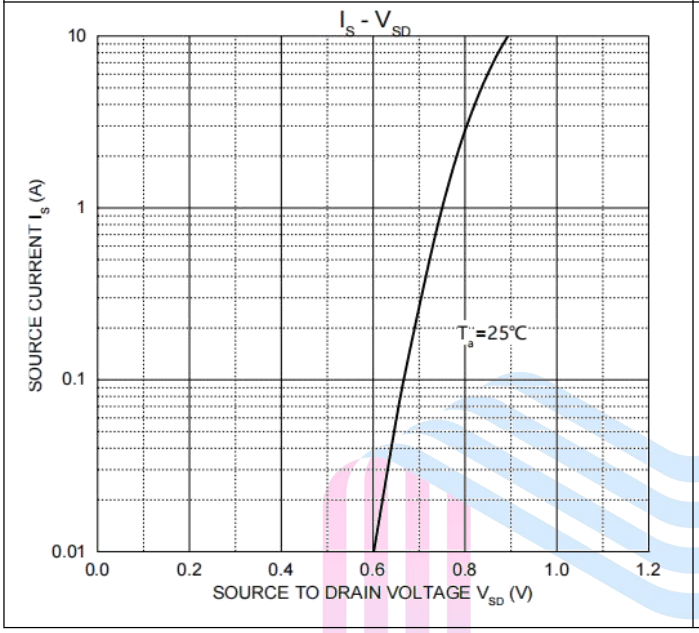
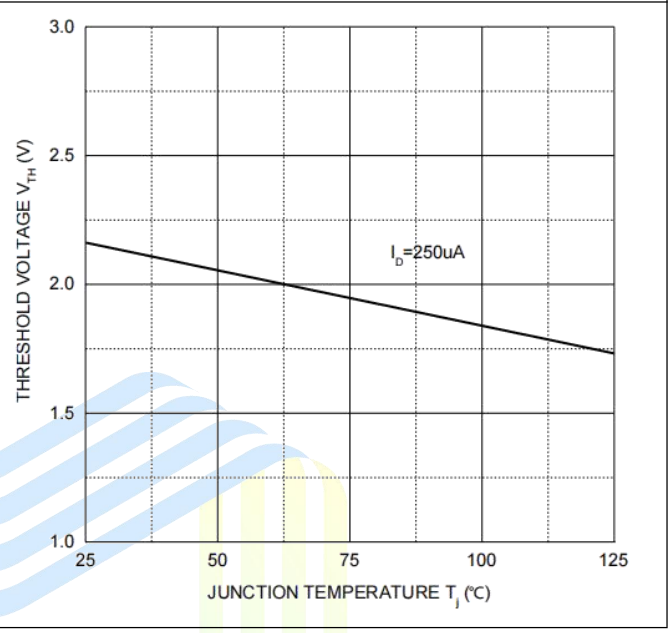
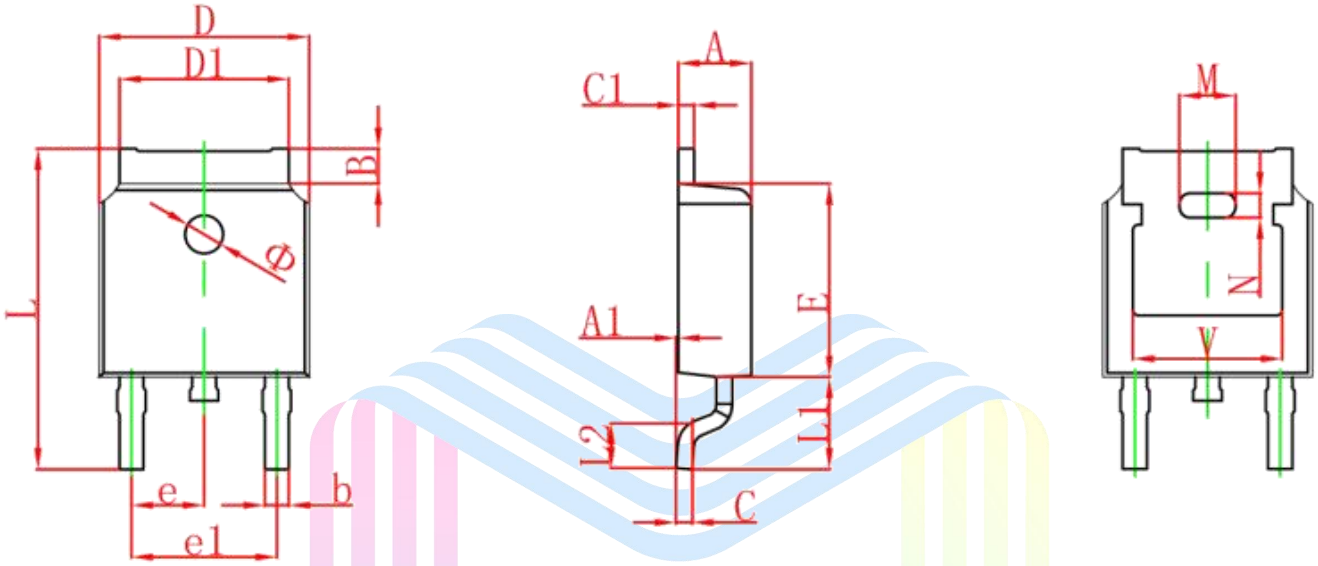


Figure 8: Threshold Voltage



Mechanical Dimensions:

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

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Via-Media Semiconductor Limited Company

http://www.vmdsemi.com

Main Sites:

- **Headquarters**

Hangzhou Via-Media Semiconductor Co., LTD.
1305-1306, Building 71, No. 90, Wensan Road, Xihu District, Hangzhou, Zhejiang Province, P.R. China
Tel: +86-0571-8515 0563

- **Chengdu Office**

Chengdu Winhi Semiconductor Co., LTD.
Floor 15, Building 5, No. 171, Hele 2nd Street, Chengdu, Sichuan Province, P.R. China
Tel: +86-028-8505 0771

- **Shanghai**

Shanghai R&D Center.
1506~1508, Xinyin Building, 888 Yishan Road, Shanghai, P.R of China
Tel: +86- 021-54201999

- **Shenzhen**

Shenzhen Sales office
Room 4A15, Block AB, Tianxiang Building, Chegongmiao , Futian District, Shenzhen, P.R of China
Tel: +86-0755- 82570682

- **Xi'an**

Xi'an R&D Center
1703B, Building A, Greenland Center, Jinye Road, High-Tech Zone, Xi'an, Shaanxi, P.R of China